L Number	Hits	Search Text	DB	Time stamp
1	75475	(laser same (power or energy))	USPAT	2004/02/26 08:32
2	670	((laser same (power or energy))) and (scribe or sribing)	USPAT	2004/02/26 08:33
3	292	(((laser same (power or energy))) and (scribe or sribing)) and (pulse or pulsing)	USPAT .	2004/02/26 08:33
4	236	(((laser same (power or energy))) and (scribe or sribing)) and ((pulse or	USPAT	2004/02/26 08:33
5	213	pulsing) same laser) (((laser same (power or energy))) and (scribe or sribing)) and ((pulse or	USPAŤ	2004/02/26 11:52
6	1	pulsing) with laser) 5168454.pn.	USPAT	2004/02/26
7	1	6281362.pn.	USPAT .	2004/02/26
_	2606	(scribe or scribing or in\$1scrib\$3) and laser and semiconductor	USPAT	2004/02/25
_	1149	((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)	USPAT	2004/02/23 12:26
<u>-</u>	543	· · · · · · · · · · · · · · · · · · ·	USPAT	2004/02/23 12:28
	284	((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and	USPAT	2004/02/23 12:28
_	278	plasma (((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and	USPAT	2004/02/23
-	263	plasma) and @ay<=2001 ((((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or	USPAT	2004/02/23
-	129	etching or remove or removing) (((((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and	USPAT	2004/02/23
-	7	(pulse or pulsing) 5149404.URPN.	USPAT	2004/02/23
-	2	5397420.URPN.	USPAT	2004/02/23
_	7	("4550257"   "4564736"   "4866238"   "4960495"   "5047649"   "5062364"   "5149404").PN.	USPAT	2004/02/23
_	9569	(mark or marking) with (substrate or wafer)	USPAT	2004/02/23
_	612	((mark or marking) with (substrate or wafer)) and laser and semiconductor and	USPAT	2004/02/23
-	405	plasma (((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium	USPAT	2004/02/23 13:43
1	1	or he or argon or Ar or N?sub.2)	L	L

	•			
	370	((((mark or marking) with (substrate or	USPAT	2004/02/23
		wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium		13:43
		or he or argon or Ar or N?sub.2)) and		
		(pit or via or hole or opening)		
-	285	(((((mark or marking) with (substrate or	USPAT	2004/02/23
		wafer)) and laser and semiconductor and		13:44
		plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and		
		(pit or via or hole or opening)) and		
		(sacrificial or photo\$1resist or resist)		
_	276	1	USPAT	2004/02/23
		wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium		13:44
		or he or argon or Ar or N?sub.2)) and		
		(pit or via or hole or opening)) and		*
		(sacrificial or photo\$1resist or resist))		
	261	and @ay<=2001 ((((((mark or marking) with (substrate	USPAT	2004/02/23
	201	or wafer)) and laser and semiconductor	OSPAI	13:49
		and plasma) and (inert or nitrogen or	:	
		helium or he or argon or Ar or N?sub.2))		
		and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist))		
		and @ay<=2001) not ((((((scribe or		
		scribing or in\$1scrib\$3) and laser and		
		semiconductor) and (pit or hole)) and		
		(inert or argon or Ar or helium or		
		nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or		
		remove or removing)) and (pulse or		
· · ·		pulsing))		X-
-	206	` ` ` ` ` ` ` ` ` ` ` ` ` ` ` ` ` ` `	USPAT	2004/02/23
		or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or		14:49
	,	helium or he or argon or Ar or N?sub.2))		
		and (pit or via or hole or opening)) and		
		(sacrificial or photo\$1resist or resist))		
		and @ay<=2001) not (((((((scribe or scribing or in\$1scrib\$3) and laser and		.
	ļ	semiconductor) and (pit or hole)) and		
	ŀ	(inert or argon or Ar or helium or	,	:
		nitrogen or He or N?sub.2)) and plasma)		
		and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or		
		pulsing))) and (depth or deep)		
-	6	("4096619"   "5023188"   "5614445"	USPAT	2004/02/23
	0070	"5691248"   "5693181"   "6075280").PN.		14:24
-	2078	(scribe or sribing) with (substrate or wafer)	USPAT	2004/02/23 14:49
-	245	((scribe or sribing) with (substrate or	USPAT	2004/02/23
		wafer)) and plasma and semiconductor and		14:50
	210	laser	HCDAT	2004/02/22
<del>-</del>	210	(((scribe or sribing) with (substrate or wafer)) and plasma and semiconductor and	USPAT	2004/02/23
		laser) not (((((((mark or marking) with		11.00
		(substrate or wafer)) and laser and		
		semiconductor and plasma) and (inert or		
	1	nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or		
		opening)) and (sacrificial or		
·		photo\$1resist or resist)) and @ay<=2001)		
		not (((((((scribe or scribing or		
		in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or		
		Ar or helium or nitrogen or He or		
		N?sub.2)) and plasma) and @ay<=2001) and		
	Δ.	(etch or etching or remove or removing))		
		and (pulse or pulsing))) and (depth or		-
		deep))	L	

			Lugara	2004/00/02
_	97	, , , , , , , , , , , , , , , , , , , ,	USPAT	2004/02/23
		wafer)) and plasma and semiconductor and		14:50
		laser) not (((((((mark or marking) with		
		(substrate or wafer)) and laser and		
		semiconductor and plasma) and (inert or		
		nitrogen or helium or he or argon or Ar		
		or N?sub.2)) and (pit or via or hole or		
		opening)) and (sacrificial or		
		photo\$1resist or resist)) and @ay<=2001)		
		not (((((((scribe or scribing or		
		in\$1scrib\$3) and laser and semiconductor)		
		and (pit or hole)) and (inert or argon or		
		Ar or helium or nitrogen or He or		
		N?sub.2)) and plasma) and @ay<=2001) and		
		(etch or etching or remove or removing))		
		and (pulse or pulsing))) and (depth or		
		deep))) and (inert or helium or argon or		
		Ar! or nitrogen or N?sub.2)		
-	90	_	USPAT	2004/02/23
		or wafer)) and plasma and semiconductor		14:51
		and laser) not (((((((mark or marking)		
		with (substrate or wafer)) and laser and		
		semiconductor and plasma) and (inert or		
		nitrogen or helium or he or argon or Ar		
		or N?sub.2)) and (pit or via or hole or		
		opening)) and (sacrificial or		
		photo\$1resist or resist)) and @ay<=2001)		
		not (((((((scribe or scribing or		
				1
		in\$1scrib\$3) and laser and semiconductor)		1
	- 10	and (pit or hole)) and (inert or argon or		
	8	Ar or helium or nitrogen or He or		1
		N?sub.2)) and plasma) and @ay<=2001) and		
		(etch or etching or remove or removing))		
	1	and (pulse or pulsing))) and (depth or		
	-	deep))) and (inert or helium or argon or		1
		Ar! or nitrogen or N?sub.2)) and (pit or		
	0.5	hole or via or trench or opening)		0004/00/00
_	85	1 , , , , , , , , , , , , , , , , , , ,	USPAT	2004/02/23
	*	or wafer)) and plasma and semiconductor		15:28
		and laser) not (((((((mark or marking)		
		with (substrate or wafer)) and laser and		
		semiconductor and plasma) and (inert or		
		nitrogen or helium or he or argon or Ar		
		or N?sub.2)) and (pit or via or hole or		
		opening)) and (sacrificial or		
		photo\$1resist or resist)) and @ay<=2001)		1.
		not (((((((scribe or scribing or		
		in\$1scrib\$3) and laser and semiconductor)		
		and (pit or hole)) and (inert or argon or		
		Ar or helium or nitrogen or He or		
	1	N?sub.2)) and plasma) and @ay<=2001) and		
		(etch or etching or remove or removing))		
	İ	and (pulse or pulsing))) and (depth or		1
	1	deep))) and (inert or helium or argon or		
	1	Ar! or nitrogen or N?sub.2)) and (pit or	1	
	1	hole or via or trench or opening)) and	1	
	1	@ay<=2001	[	
_	1	1	USPAT	2004/02/23
		•		15:29
_	660	laser and (scribe or scribing) and	USPAT	2004/02/23
	1	semiconductor and plasma		15:30

-	570	(laser and (scribe or scribing) and	USPAT	2004/02/23
		semiconductor and plasma) not		15:30
		(((((scribe or sribing) with (substrate		
		or wafer)) and plasma and semiconductor		
	8	and laser) not (((((((mark or marking)		
		with (substrate or wafer)) and laser and		
		semiconductor and plasma) and (inert or		
		nitrogen or helium or he or argon or Ar		•
		or N?sub.2)) and (pit or via or hole or		
		opening)) and (sacrificial or		
		photo\$1resist or resist)) and @ay<=2001)		
		not (((((((scribe or scribing or		
		in\$1scrib\$3) and laser and semiconductor)		
		and (pit or hole)) and (inert or argon or		
		Ar or helium or nitrogen or He or		
		N?sub.2)) and plasma) and @ay<=2001) and		
		(etch or etching or remove or removing))		
		and (pulse or pulsing))) and (depth or		
		deep))) and (inert or helium or argon or		
		Ar! or nitrogen or N?sub.2)) and (pit or		-
		hole or via or trench or opening))		
	462	((laser and (scribe or scribing) and	USPAT	2004/02/23
-	402	' '	ODENI	15:31
		semiconductor and plasma) not		10:21
	7	((((((scribe or sribing) with (substrate		
		or wafer)) and plasma and semiconductor	,	
	·	and laser) not (((((((mark or marking)		
		with (substrate or wafer)) and laser and		
		semiconductor and plasma) and (inert or		
		nitrogen or helium or he or argon or Ar		
}		or N?sub.2)) and (pit or via or hole or	,	
		opening)) and (sacrificial or		
		photo\$1resist or resist)) and @ay<=2001)		
		not (((((((scribe or scribing or		
		in\$1scrib\$3) and laser and semiconductor)		
		and (pit or hole)) and (inert or argon or		
1		Ar or helium or nitrogen or He or	·	
		N?sub.2)) and plasma) and @ay<=2001) and		
		(etch or etching or remove or removing))		
		and (pulse or pulsing))) and (depth or		ļ
		deep))) and (inert or helium or argon or		
		Ar! or nitrogen or N?sub.2)) and (pit or		
		hole or via or trench or opening))) and		
				j
		@ay<=2001 and (hole or pit or via or		ļ
·	0.40	trench or opening)	***	2004/02/22
-	249	(((laser and (scribe or scribing) and	USPAT	2004/02/23
		semiconductor and plasma) not		15:32
		(((((scribe or sribing) with (substrate		
,		or wafer)) and plasma and semiconductor	1	
		and laser) not (((((((mark or marking)		
-		with (substrate or wafer)) and laser and		
		semiconductor and plasma) and (inert or		
		nitrogen or helium or he or argon or Ar		
		or N?sub.2)) and (pit or via or hole or		.
9		opening)) and (sacrificial or		
1		photo\$1resist or resist)) and @ay<=2001)		
		not (((((((scribe or scribing or		
		in\$1scrib\$3) and laser and semiconductor)		
1		and (pit or hole)) and (inert or argon or		
1		Ar or helium or nitrogen or He or		·
		N?sub.2)) and plasma) and @ay<=2001) and		
		(etch or etching or remove or removing))		*
		and (pulse or pulsing))) and (depth or		
		deep))) and (inert or helium or argon or		
		Ar! or nitrogen or N?sub.2)) and (pit or		
		hole or via or trench or opening))) and		2
		@ay<=2001 and (hole or pit or via or		
		trench or opening)) and (inert or helium		
1	I	or argon or Ar! or nitrogen or N?sub.2)		l

_	8	Peiter-Martin.in.	USPAT;	2004/02/25
			US-PGPUB;	17:36
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	15	Marx-Eckhard.in.	USPAT;	2004/02/25
			US-PGPUB;	17:36
			EPO; JPO;	
· · ·			DERWENT;	
			IBM_TDB	
-	15	Mautz-Karl-E.in.	USPAT;	2004/02/25
			US-PGPUB;	17:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	33	Peiter-Martin.in. or Marx-Eckhard.in. or	USPAT;	2004/02/25
		Mautz-Karl-E.in.	US-PGPUB;	17:36
	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	